Abstracts

Characterizing the gate to source nonlinear capacitor role on FET IMD performance

J.A. Garcia, A. Mediavilla, J.C. Pedro, N.B. Carvalho, A. Tazon and J.L. Garcia. "Characterizing the gate to source nonlinear capacitor role on FET IMD performance." 1998 MTT-S International Microwave Symposium Digest 98.3 (1998 Vol. III [MWSYM]): 1635-1638.

This paper discusses the gate to source nonlinear capacitor contribution on small signal intermodulation distortion (IMD) performance of FET devices. The second and third order coefficients for the Cgs(Vgs) Taylor-series expansion, experimentally extracted with a simplified one-sided version of our previously proposed test set-up, are shown to be responsible for some detected differences on IMD behaviour at high frequencies.

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